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View Online at https://aerobasegroup.com/nsn/5961-00-883-0110
Inclosure Material:
Metal
Overall Length:
3.327 inches
Overall Diameter:
1.227 inches
Mounting Facility Quantity:
1
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-94
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Overall Width Across Flats:
1.047 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
600.0 forward voltage, peak and 720.0 reverse voltage, instantaneous and 750.0 reverse voltage, peak and 10.0 forward gate to source
voltage and 5.0 reverse gate to source voltage
Current Rating Per Characteristic:
2.00 amperes zero-gate-voltage source current horsepower metric
Power Rating Per Characteristic:
5.0 watts small-signal input power, common-collector blank and 0.5 watts any acceptable universal
Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius case

Special Features:

One cathode lead (small wire w/lug) may be cut off if not needed.

Thread Series Designator:

Unf

Terminal Type And Quantity:

3 insulated wire lead w/terminal lug and 1 threaded stud

Specification Data:

80131-release4287 professional/industrial association specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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